

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

March 1997

Features

- Fully Static Operation
- Industry Standard 1024 x 4 Pinout (Same as Pinouts for 6514, 2114, 9114, and 4045 Types)
- Common Data Input and Output
- Memory Retention for Standby Battery Voltage as Low as 2V Min
- All Inputs and Outputs Directly TTL Compatible
- Three-State Outputs
- Low Standby and Operating Power

Description

The MWS5114 is a 1024 word by 4-bit static random access memory that uses the ion-implanted silicon gate complementary MOS (CMOS) technology. It is designed for use in memory systems where low power and simplicity in use are desirable. This type has common data input and data output and utilizes a single power supply of 4.5V to 6.5V.

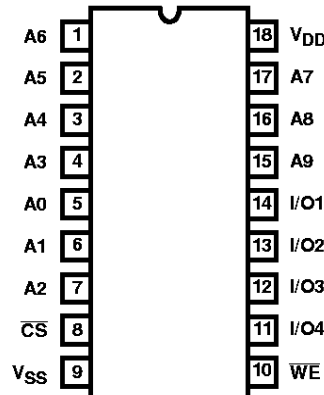
The MWS5114 is supplied in 18 lead, hermetic, dual-in-line sidebraced ceramic packages (D suffix) and in 18 lead dual-in-line plastic packages (E suffix).

Ordering Information

200ns	250ns	300ns	TEMPERATURE RANGE	PACKAGE	PKG. NO.
MWS5114E3	MWS5114E2 MWS5114E2X	MWS5114E1	0°C to +70°C	PDIP Burn-In	E18.3 E18.3
MWS5114D3 MWS5114D3X	MWS5114D2	MWS5114D1	0°C to +70°C	SBDIP Burn-In	D18.3 D18.3

Pinout

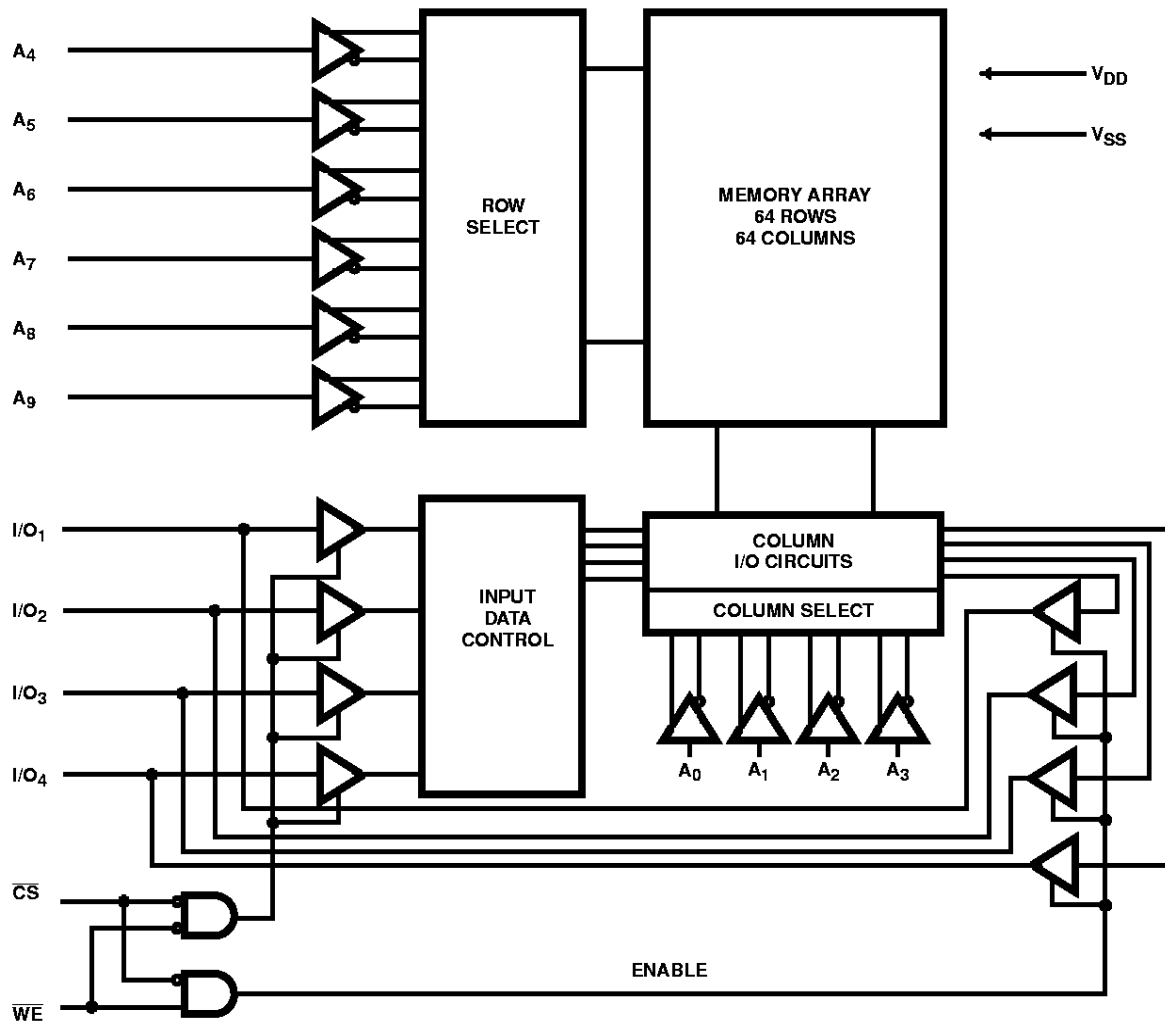
MWS5114
(PDIP, SBDIP)
TOP VIEW



OPERATIONAL MODES

FUNCTION	\overline{CS}	\overline{WE}	DATA PINS
Read	0	1	Output: Dependent on data
Write	0	0	Input
Not Selected	1	X	High Impedance

Functional Block Diagram



MWS5114

Absolute Maximum Ratings

DC Supply Voltage Range, (V_{DD})
 (All Voltages Referenced to V_{SS} Terminal) -0.5V to +7V
 Input Voltage Range, All Inputs -0.5V to $V_{DD} + 0.5V$
 DC Input Current, Any One Input $\pm 10mA$

Thermal Information

Thermal Resistance (Typical) θ_{JA} ($^{\circ}C/W$) θ_{JC} ($^{\circ}C/W$)
 Plastic DIP Package 75 N/A
 SBDIP Package 75 20
 Operating Temperature Range (T_A)
 Package Type D -55 $^{\circ}C$ to +125 $^{\circ}C$
 Package Type E -40 $^{\circ}C$ to +85 $^{\circ}C$
 Maximum Storage Temperature Range (T_{STG}) -65 $^{\circ}C$ to +150 $^{\circ}C$
 Maximum Junction Temperature
 Ceramic Package +175 $^{\circ}C$
 Plastic Package +150 $^{\circ}C$
 Maximum Lead Temperature +265 $^{\circ}C$

Recommended Operating Conditions

At T_A = Full Package Temperature Range. For maximum reliability, operating conditions should be selected so that operation is always within the following ranges:

PARAMETER	LIMITS		UNITS
	ALL TYPES		
	MIN	MAX	
DC Operating Voltage Range	4.5	6.5	V
Input Voltage Range	V_{SS}	V_{DD}	V

Static Electrical Specifications

At $T_A = 0^{\circ}C$ to +70 $^{\circ}C$, $V_{DD} = \pm 5\%$, Except as Noted

PARAMETER	SYMBOL	CONDITIONS			LIMITS									UNITS
		V_O (V)	V_{IN} (V)	V_{DD} (V)	MWS5114-3			MWS5114-2			MWS5114-1			
					MIN	(NOTE 1) TYP	MAX	MIN	(NOTE 1) TYP	MAX	MIN	(NOTE 1) TYP	MAX	
Quiescent Device Current	IDD	-	0, 5	5	-	75	100	-	75	100	-	75	250	μA
Output Low (Sink) Current	I_{OL}	0.4	0, 5	5	2	4	-	2	4	-	2	4	-	mA
Output High (Source) Current	I_{OH}	4.6	0, 5	5	-0.4	-1	-	-0.4	-1	-	-0.4	-1	-	mA
Output Voltage Low-Level	VOL	-	0, 5	5	-	0	0.1	-	0	0.1	-	0	0.1	V
Output Voltage High-Level	VOH	-	0, 5	5	4.9	5	-	4.9	5	-	4.9	5	-	V
Input Low Voltage	V_{IL}	0.5, 4.5	-	5	-	1.2	0.8	-	1.2	0.8	-	1.2	0.8	V
Input High Voltage	V_{IH}	0.5, 4.5	-	5	2.4	-	-	2.4	-	-	2.4	-	-	V
Input Leakage Current (Note 2)	IIN	-	0, 5	5	-	± 0.1	± 5	-	± 0.1	± 5	-	± 0.1	± 5	μA
Operating Current (Note 3)	IDD1	-	0, 5	5	-	4	8	-	4	8	-	4	8	mA

MWS5114

Static Electrical Specifications At $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{DD} = \pm 5\%$, Except as Noted (Continued)

PARAMETER	SYMBOL	CONDITIONS			LIMITS									UNITS
		V_O (V)	V_{IN} (V)	V_{DD} (V)	MWS5114-3			MWS5114-2			MWS5114-1			
					MIN	(NOTE 1) TYP	MAX	MIN	(NOTE 1) TYP	MAX	MIN	(NOTE 1) TYP	MAX	
Three-State Output Leakage Current (Note 4)	I_{OUT}	0, 5	0, 5	5	-	± 0.5	± 5	-	± 0.5	± 5	-	± 0.5	± 5	μA
Input Capacitance	C_{IN}	-	-	-	-	5	7.5	-	5	7.5	-	5	7.5	pF
Output Capacitance	C_{OUT}	-	-	-	-	10	15	-	10	15	-	10	15	pF

NOTES:

1. Typical values are for $T_A = 25^\circ\text{C}$ and nominal V_{DD} .
2. All inputs in parallel.
3. Outputs open circuited; cycle time = $1\mu\text{s}$.
4. All outputs in parallel.

MWS5114

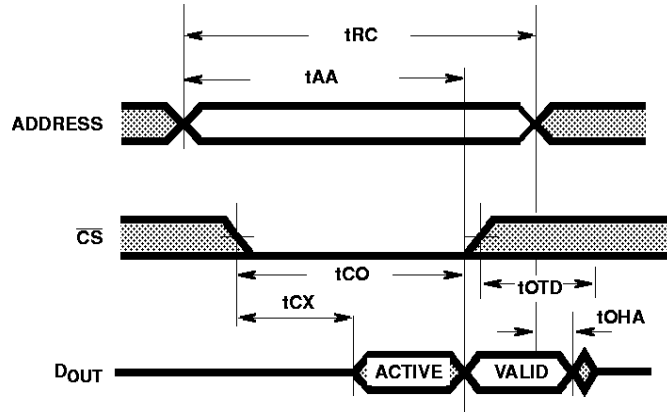
Dynamic Electrical Specifications at $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{DD} = 5V \pm 5\%$, Input $t_R, t_F = 10\text{ns}$; $C_L = 50\text{pF}$ and 1 TTL Load

PARAMETER	SYMBOL	LIMITS									UNITS
		MWS5114-3			MWS5114-2			MWS5114-1			
		(NOTE 1) MIN	(NOTE 2) TYP	MAX	(NOTE 1) MIN	(NOTE 2) TYP	MAX	(NOTE 1) MIN	(NOTE 2) TYP	MAX	
READ CYCLE TIMES (FIGURE 1)											
Read Cycle	t _{RC}	200	160	-	250	200	-	300	250	-	ns
Access from Address	t _{AA}	-	160	200	-	200	250	-	250	300	ns
Chip Selection to Output Valid	t _{CO}	-	110	150	-	150	200	-	200	250	ns
Chip Selection to Output Active	t _{CX}	20	100	-	20	100	-	20	100	-	ns
Output Three-State from Deselection	t _{OTD}	-	75	125	-	75	125	-	75	125	ns
Output Hold from Address Change	t _{OHA}	50	100	-	50	100	-	50	100	-	ns
WRITE CYCLE TIMES (FIGURE 2)											
Write Cycle	t _{WC}	200	160	-	250	200	-	300	220	-	ns
Write	t _W	125	100	-	150	120	-	200	140	-	ns
Write Release	t _{WR}	50	40	-	50	40	-	50	40	-	ns
Address to Chip Select Setup Time	t _{ACS}	0	0	-	0	0	-	0	0	-	ns
Address to Write Setup Time	t _{AW}	25	20	-	50	40	-	50	40	-	ns
Data to Write Setup Time	t _{DSU}	75	50	-	75	50	-	75	50	-	ns
Data Hold from Write	t _{DH}	30	10	-	30	10	-	30	10	-	ns

NOTES:

1. Time required by a limit device to allow for the indicated function.
2. Typical values are for $T_A = 25^\circ\text{C}$ and nominal V_{DD} .

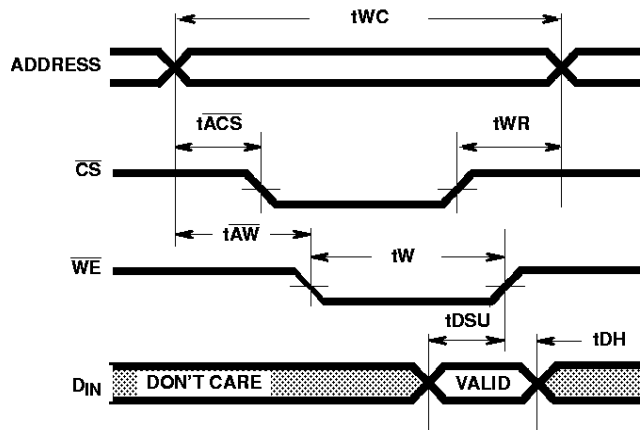
MWS5114



NOTE:

- \overline{WE} is high during the Read Cycle. Timing measurement reference level is 1.5V.

FIGURE 1. READ CYCLE TIMING WAVEFORMS



NOTE:

- \overline{WE} is low during the Write Cycle. Timing measurement reference level is 1.5V.

FIGURE 2. WRITE CYCLE TIMING WAVEFORMS

Data Retention Specifications at $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$; See Figure 3

PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS			UNITS	
		V_{DR} (V)	V_{DD} (V)	ALL TYPES				
				MIN	(NOTE 1) TYP	MAX		
Minimum Data Retention Voltage	VDR	-	-	2	-	-	V	
Data Retention Quiescent Current	MWS5114-3	IDD	2	-	-	25	50	μA
	MWS5114-2		2	-	-	25	50	μA
	MWS5114-1		2	-	-	60	125	μA
Chip Deselect to Data Retention Time	tCDR	-	5	300	-	-	ns	
Recovery to Normal Operation Time	tRC	-	5	300	-	-	ns	
V_{DD} to V_{DR} Rise and Fall Time	t _R , t _F	2	5	1	-	-	μs	

NOTE:

- Typical Values are for $T_A = 25^\circ\text{C}$ and nominal V_{DD} .

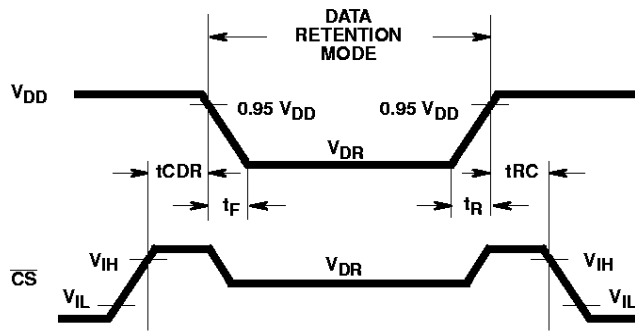


FIGURE 3. LOW V_{DD} DATA RETENTION TIMING WAVEFORMS